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APPLICATION NO.	F	TLING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
09/826,472	326,472 04/04/2001		Bin Yu	0180197	6214	
25700	7590	03/03/2004		EXAM	EXAMINER	
FARJAMI	& FARJ	AMI LLP	POMPEY, RON EVERETT			
16148 SAND CANYON IRVINE, CA 92618				ART UNIT	PAPER NUMBER	
				2812		
				DATE MAILED: 03/03/2004	DATE MAILED: 03/03/2004	

Please find below and/or attached an Office communication concerning this application or proceeding.

			- In				
	Application No.	Applicant(s)	-				
	09/826,472	YU, BIN					
Office Action Summary	Examiner	Art Unit					
	Ron E Pompey	2812					
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with	the correspondence addre	ess				
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	I36(a). In no event, however, may a reply within the statutory minimum of thirty will apply and will expire SIX (6) MONT a, cause the application to become ABA	oly be timely filed (30) days will be considered timely. HS from the mailing date of this comm NDONED (35 U.S.C. § 133).	nunication.				
Status							
1) Responsive to communication(s) filed on 26 J	anuary 2004.						
	s action is non-final.						
,—	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under I	Ex parte Quayle, 1935 C.D.	11, 453 O.G. 213.					
Disposition of Claims							
4) ☐ Claim(s) 1-3 and 5-19 is/are pending in the ap 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-3 and 5-19 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	wn from consideration.						
Application Papers			•				
9) The specification is objected to by the Examine	er.						
10)☐ The drawing(s) filed on is/are: a)☐ acc	cepted or b) objected to b	y the Examiner.					
Applicant may not request that any objection to the	• ,	, ,					
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E.							
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureat * See the attached detailed Office action for a list	ts have been received. ts have been received in Ap prity documents have been r nu (PCT Rule 17.2(a)).	oplication No received in this National St	age				
Attachment(s)	_						
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)		ımmary (PTO-413) /Mail Date					
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 		ormal Patent Application (PTO-1	52)				

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- Claims 1-3 and 5-19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Gardner et al. (US 5,963,810) and further in view of Dautartas et al. (US 6,124,158), Chen (US 5,994,192), admitted prior art and Adetutu et al. (US 6,369,430).
 Gardner discloses the limitations of:

For 1, 2, 5-6, 8, 9, 11, 12 and 14:

depositing a first nitride film (303, fig. 3A) on a semiconductor substrate; depositing a high-k material (305, fig. 3B) on the first nitride (col. 5, Ins. 30-64 and col. 3, Ins. 25-32),

depositing a second nitride film on the high-k material (col. 6, Ins. 13-20); depositing a thick gate material on the second ultra-thin nitride film; and completing fabrication of the device;

wherein the first and second ultra-thin nitride films prevent the at least one material selected from the group consisting essentially of zirconium (Zr), hafnium (Hf) and titanium (Ti) from diffusing into the semiconductor substrate and the thick gate material respectively (col. 6, Ins. 1-12). It is inherent that the diffusion of the metal material will be prevented, because the structure of the gate dielectric (nitride/high

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k/nitride) of Gardner is the same as that of applicants claimed invention and therefore will perform the same.

3. Gardner does not disclose the claimed limitation(s) of, for claims 3, 7, 13 and 15-30:

wherein the nitride films are deposited by using an atomic layer deposition (ALD) technique.

However, Dautartas discloses the above claimed limitations in column 7, line(s) 15-30.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine Dautartas with Gardner, because this deposition technique provides excellent uniformity and surface conformity of thin insulator films..

Gardner does not disclose the claimed limitation(s) of, for claims 10 and 18-19:
 that using a photoresist is part of the etching processes.

However, Chen discloses the above claimed limitations in column 4, line(s) 14-34.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine Chen with Gardner, because photoresist protects the area that is not being removed during formation of the gate structure and to supply applicant with further support for the *official notice* stated in the office action mailed 8-20-02.

5. Gardner does not disclose the claimed limitation(s) of, for claim 1 and 12:

Wherein the thin metal film comprises at least one material selected form the group consisting essentially of zirconium (Zr), hafnium (Hf) and titanium(Ti).

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However, the admitted prior art discloses the above claimed limitations on page2, line(s) 1-8.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine the admitted prior art with Gardner, because they are art recognized equivalent materials.

6. Gardner does not disclose the claimed limitation(s) of, for claims 2 and 12: wherein the substrate comprises a silicon-on-insulator (SOI) wafer.

However, Adetutu discloses the above claimed limitations in column 2, line(s) 25-27.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to combine Adetutu with Gardner, because the SOI substrate reduces the body capacitance of a semiconductor device.

Claim Objections

7. Claims 1 and 12 are objected to because of the following informalities: the language thick is not quantified in the specification and is held to make the claim indefinite. Appropriate correction is required.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E Pompey whose telephone number is (571) 272-1680. The examiner can normally be reached on flex schedule.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Ron Pompey

AU: 2812

February 20, 2004

Wonn F. Niebling

Supervisory Patent Examiner Technology Center 2800